



STW8NB90

N - CHANNEL 900V - 1.1Ω - 8A - TO-247 PowerMESH™ MOSFET

PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STW8NB90	900 V	< 1.45 Ω	8 A

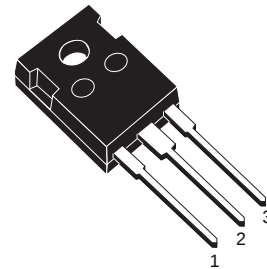
- TYPICAL R_{DS(on)} = 1.1 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- VERY LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED

DESCRIPTION

Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performances. The new patent pending strip layout coupled with the Company's proprietary edge termination structure, gives the lowest R_{DS(on)} per area, exceptional avalanche and dv/dt capabilities and unrivalled gate charge and switching characteristics.

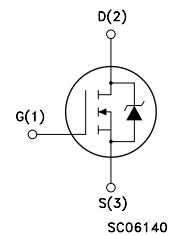
APPLICATIONS

- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVE
- HIGH CURRENT, HIGH SPEED SWITCHING



TO-247

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	900	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	900	V
V _{GS}	Gate-source Voltage	± 30	V
I _D	Drain Current (continuous) at T _c = 25 °C	8	A
I _D	Drain Current (continuous) at T _c = 100 °C	5	A
I _{DM} (•)	Drain Current (pulsed)	32	A
P _{tot}	Total Dissipation at T _c = 25 °C	190	W
	Derating Factor	1.52	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	4	V/ns
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(•) Pulse width limited by safe operating area

(1) I_{SD} ≤ 8 A, ≤ 200 A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	0.66	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	30	°C/W
R _{thc-sink}	Thermal Resistance Case-sink	Typ	0.1	°C/W
T _I	Maximum Lead Temperature For Soldering Purpose		300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive	8	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	700	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA V _{GS} = 0	900			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _c = 100 °C			1 50	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 30 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 µA	3	4	5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V I _D = 4 A		1.1	1.45	Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} × R _{DS(on)max} V _{GS} = 10 V	8			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} I _D = 4 A	1.5	8		S
C _{iss}	Input Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		2120	2865	pF
C _{oss}	Output Capacitance			225	305	pF
C _{rss}	Reverse Transfer Capacitance			23	31	pF

ELECTRICAL CHARACTERISTICS (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 450\text{ V}$ $I_D = 3.5\text{ A}$		25	35	ns
t_r	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		12	16	ns
Q_g	Total Gate Charge	$V_{DD} = 720\text{ V}$ $I_D = 7.4\text{ A}$ $V_{GS} = 10\text{ V}$		51	72	nC
Q_{gs}	Gate-Source Charge	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		12.5		nC
Q_{gd}	Gate-Drain Charge			23.5		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 720\text{ V}$ $I_D = 7.4\text{ A}$		22	31	ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		15	21	ns
t_c	Cross-over Time			31	44	ns

SOURCE DRAIN DIODE

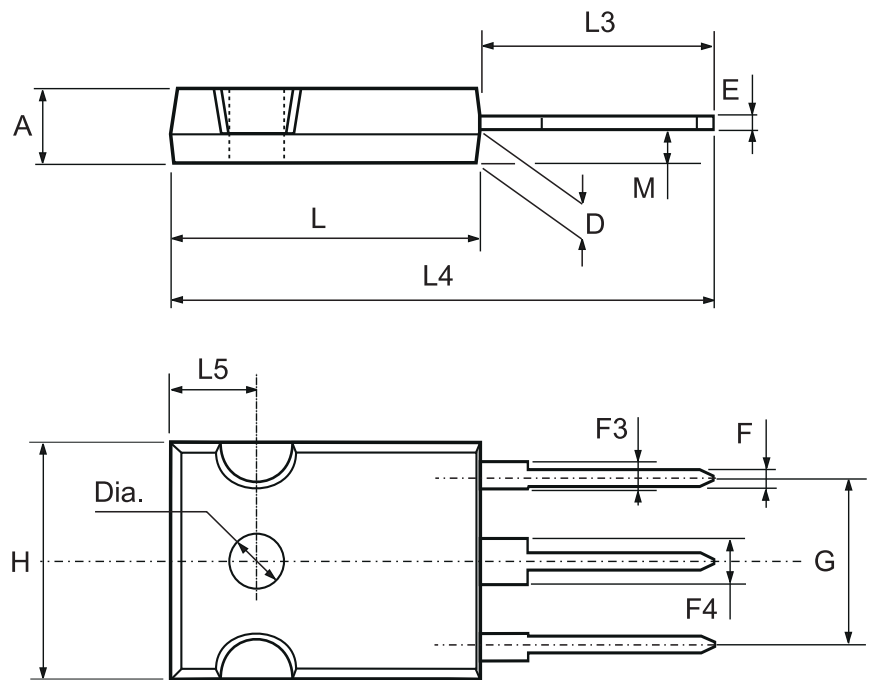
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				8	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				32	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 8\text{ A}$ $V_{GS} = 0$			1.6	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 7.4\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		700		ns
Q_{rr}	Reverse Recovery Charge			6.3		μC
I_{RRM}	Reverse Recovery Current			18		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

TO-247 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		5.3	0.185		0.209
D	2.2		2.6	0.087		0.102
E	0.4		0.8	0.016		0.031
F	1		1.4	0.039		0.055
F3	2		2.4	0.079		0.094
F4	3		3.4	0.118		0.134
G		10.9			0.429	
H	15.3		15.9	0.602		0.626
L	19.7		20.3	0.776		0.779
L3	14.2		14.8	0.559	0.413	0.582
L4		34.6			1.362	
L5		5.5			0.217	
M	2		3	0.079		0.118
Dia	3.55		3.65	0.140		0.144



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